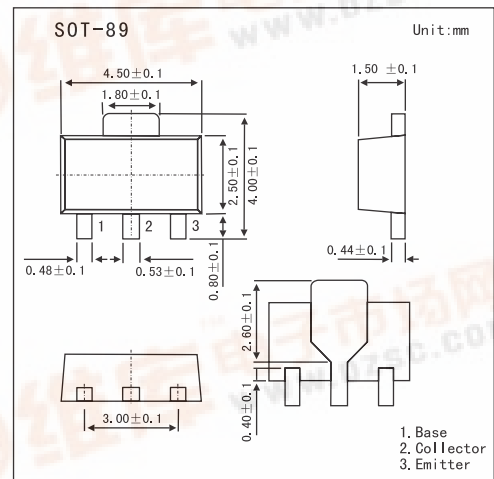


SMD Type Transistors

Silicon PNP Epitaxial Planar Type  
2SB766,2SB766A

■ Features

- Large collector power dissipation PC
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	2SB766	-30
		2SB766A	-60
Collector-emitter voltage	V <sub>CEO</sub>	2SB766	-25
		2SB766A	-50
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	I <sub>C</sub>	-1	A
Peak collector current	I <sub>CP</sub>	-1.5	A
Collector power dissipation	P <sub>C</sub>	-1	W
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

**2SB766,2SB766A**

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base voltage	2SB766	Ic = -10 $\mu$ A, IE = 0	-30			V
	2SB766A		-60			
Collector-emitter voltage	2SB766	Ic = -2 mA, IB = 0	-25			V
	2SB766A		-50			
Emitter-base voltage	VEBO	IE = -10 $\mu$ A, IC = 0	-5			V
Collector-base cutoff current	ICBO	VCB = -20 V, IE = 0			-0.1	nA
Forward current transfer ratio	hFE	VCE = -10 V, IC = -500 mA	85		340	
		VCE = -5 V, IC = -1 A	50			
Collector-emitter saturation voltage	VCE(sat)	IC = -500 mA, IB = -50 mA		-0.2	-0.4	V
Base-emitter saturation voltage	VBE(sat)	IC = -500 mA, IB = -50 mA		-0.85	-1.2	V
Transition frequency	fT	VCB = -10 V, IE = 50 mA, f = 200 MHz		200		MHz
Collector output capacitance	Cob	VCB = -10 V, IE = 0, f = 1 MHz		20	30	pF

## ■ hFE Classification

Marking	2SB766(A)/2SB766A(B)		
Rank	Q	R	S
hFE	85~170	120~240	17~340